

# MBR4015LWT

## SWITCHMODE™ Schottky Power Rectifier TO247 Power Package

This device employs the Schottky Barrier principle in a large area metal-to-silicon power rectifier. Features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency switching power supplies; free wheeling diodes and polarity protection diodes.

### Features

- Highly Stable Oxide Passivated Junction
- Guardring for Overvoltage Protection
- Low Forward Voltage Drop
- Dual Diode Construction; Terminals 1 and 3 May Be Connected for Parallel Operation at Full Rating.
- Full Electrical Isolation without Additional Hardware
- Pb-Free Package is Available\*

### Mechanical Characteristics

- Case: Molded Epoxy
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 4.3 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

### MAXIMUM RATINGS

| Rating                                                                                                                        | Symbol                          | Value       | Unit             |
|-------------------------------------------------------------------------------------------------------------------------------|---------------------------------|-------------|------------------|
| Peak Repetitive Reverse Voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage                                        | $V_{RRM}$<br>$V_{RWM}$<br>$V_R$ | 15          | V                |
| Average Rectified Forward Current<br>(At Rated $V_R$ , $T_C = 120^\circ\text{C}$ )<br>Per Leg<br>Per Package                  | $I_O$                           | 20<br>40    | A                |
| Peak Repetitive Forward Current,<br>(At Rated $V_R$ , Square Wave,<br>20 kHz, $T_C = 95^\circ\text{C}$ )<br>Per Leg           | $I_{FRM}$                       | 40          | A                |
| Non-Repetitive Peak Surge Current<br>(Surge Applied at Rated Load<br>Conditions Halfwave, Single Phase,<br>60 Hz) Per Package | $I_{FSM}$                       | 120         | A                |
| Storage/Operating Case Temperature                                                                                            | $T_{stg}, T_C$                  | -55 to +150 | °C               |
| Operating Junction Temperature (Note 1)                                                                                       | $T_J$                           | -55 to +150 | °C               |
| Voltage Rate of Change,<br>(Rated $V_R$ , $T_J = 25^\circ\text{C}$ )                                                          | $dv/dt$                         | 10,000      | V/ $\mu\text{s}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

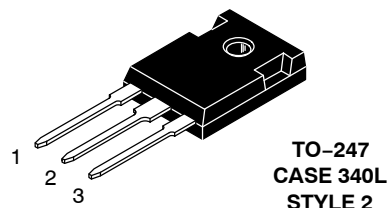
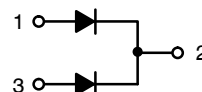
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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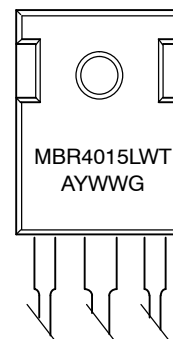
<http://onsemi.com>

## SCHOTTKY BARRIER RECTIFIER 40 AMPERES, 15 VOLTS



TO-247  
CASE 340L  
STYLE 2

### MARKING DIAGRAM



MBR4015LWT = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

| Device      | Package             | Shipping        |
|-------------|---------------------|-----------------|
| MBR4015LWT  | TO-247              | 30 Units / Rail |
| MBR4015LWTG | TO-247<br>(Pb-Free) | 30 Units / Rail |

# MBR4015LWT

## THERMAL CHARACTERISTICS

| Rating                               | Symbol          | Value | Unit                 |
|--------------------------------------|-----------------|-------|----------------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 0.57  | $^{\circ}\text{C/W}$ |
| Junction-to-Ambient                  | $R_{\theta JA}$ | 55    | $^{\circ}\text{C/W}$ |

## ELECTRICAL CHARACTERISTICS

| Rating                                                                                                                      | Symbol | Value                                                                                 | Unit |
|-----------------------------------------------------------------------------------------------------------------------------|--------|---------------------------------------------------------------------------------------|------|
| Maximum Instantaneous Forward Voltage (Note 2), See Figure 2 Per Leg<br>( $I_F = 20\text{ A}$ )<br>( $I_F = 40\text{ A}$ )  | $V_F$  | $T_J = 25^{\circ}\text{C}$<br>0.42<br>$T_J = 100^{\circ}\text{C}$<br>0.36<br>0.48     | V    |
| Maximum Instantaneous Reverse Current (Note 2), See Figure 4 Per Leg<br>( $V_R = 15\text{ V}$ )<br>( $V_R = 7.5\text{ V}$ ) | $I_R$  | $T_J = 25^{\circ}\text{C}$<br>5.0<br>$T_J = 100^{\circ}\text{C}$<br>530<br>2.7<br>370 | mA   |

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .
- Pulse Test: Pulse Width  $\leq 250\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

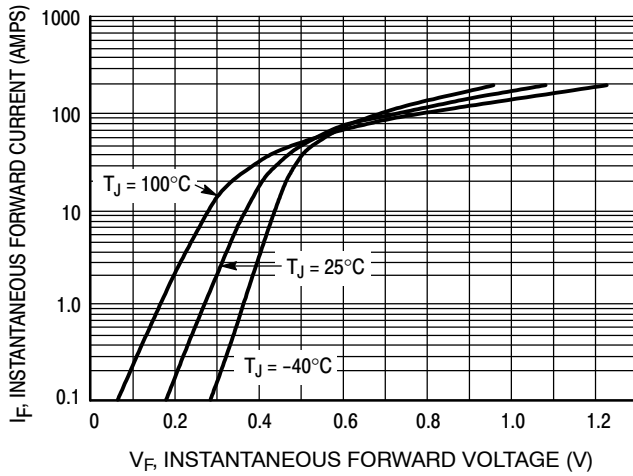


Figure 1. Typical Forward Voltage Per Leg

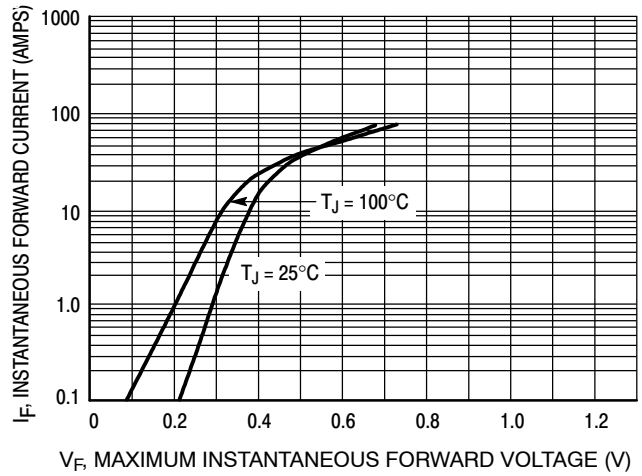


Figure 2. Maximum Forward Voltage Per Leg

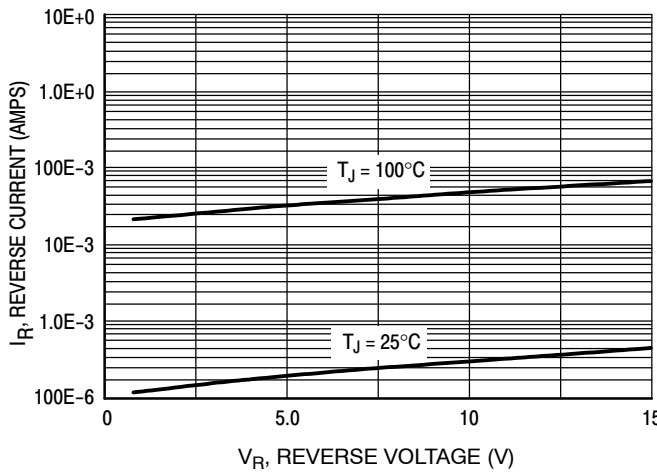


Figure 3. Typical Reverse Current Per Leg

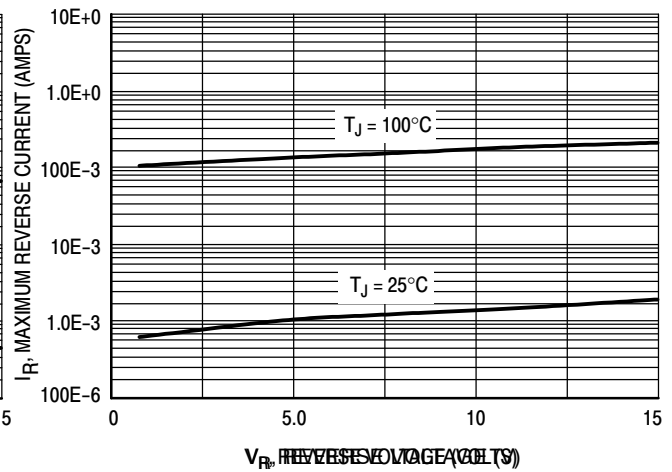


Figure 4. Maximum Reverse Current Per Leg

# MBR4015LWT

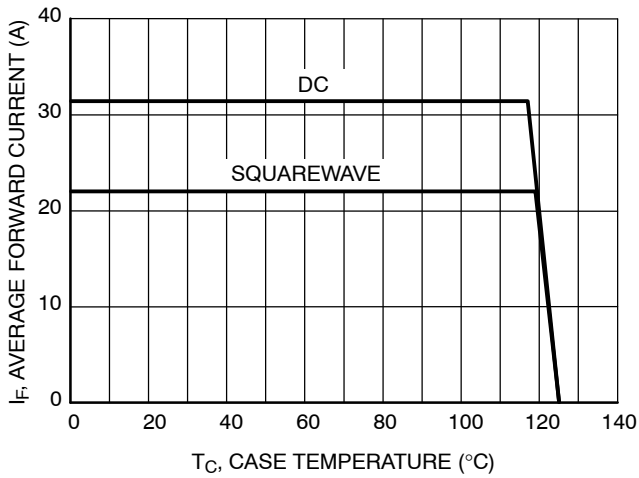


Figure 5. Current Derating Per Leg

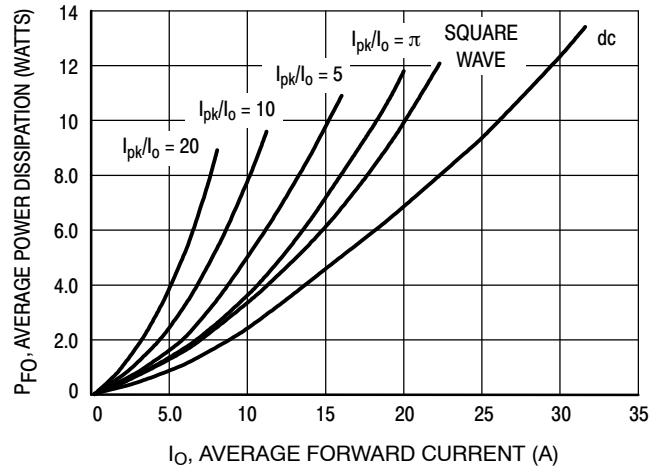


Figure 6. Forward Power Dissipation Per Leg

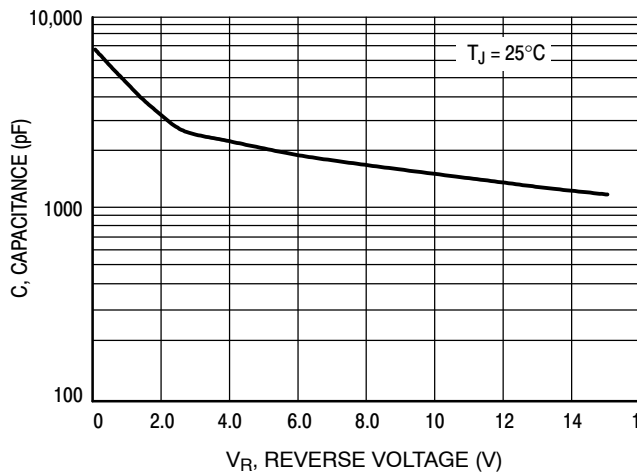


Figure 7. Capacitance Per Leg

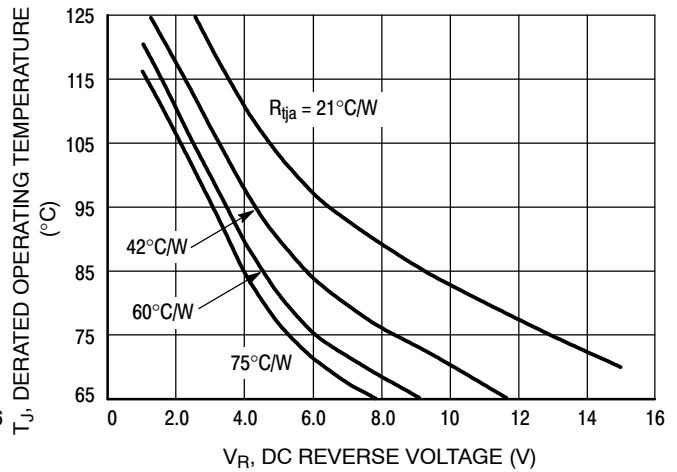


Figure 8. Typical Operating Temperature Derating Per Leg\*

\*Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of  $T_J$  therefore must include forward and reverse power effects. The allowable operating  $T_J$  may be calculated from the equation:  $T_J = T_{Jmax} - r(t)(P_f + P_r)$  where

$r(t)$  = thermal impedance under given conditions,

$P_f$  = forward power dissipation, and

$P_r$  = reverse power dissipation

This graph displays the derated allowable  $T_J$  due to reverse bias under DC conditions only and is calculated as  $T_J = T_{Jmax} - r(t)P_r$ , where  $r(t) = R_{thja}$ . For other power applications further calculations must be performed.

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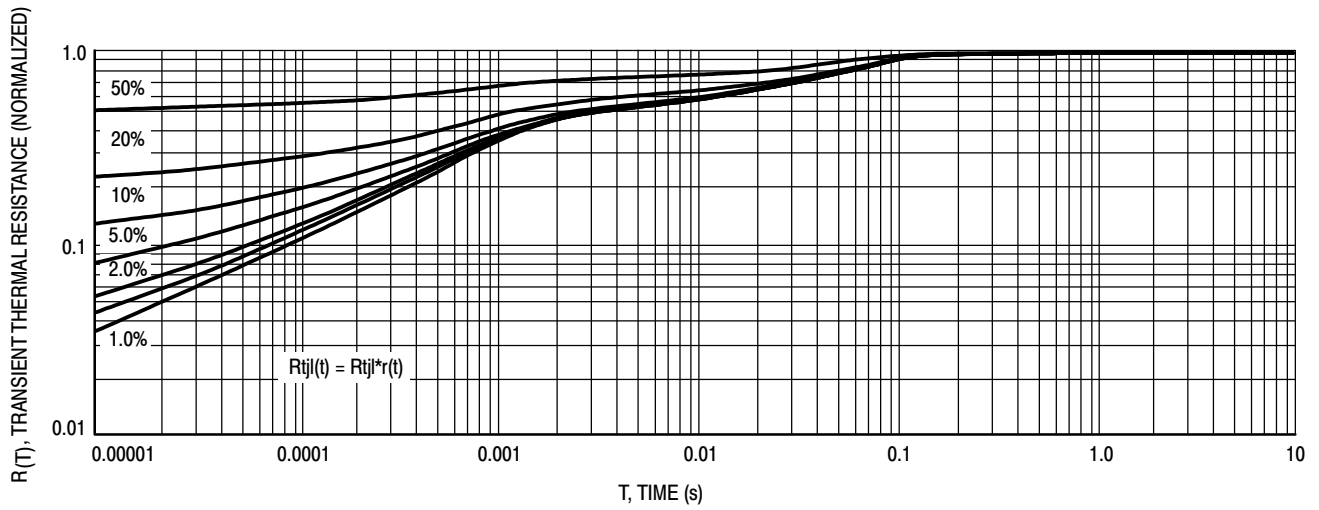


Figure 9. Thermal Response Junction to Lead (Per Leg)

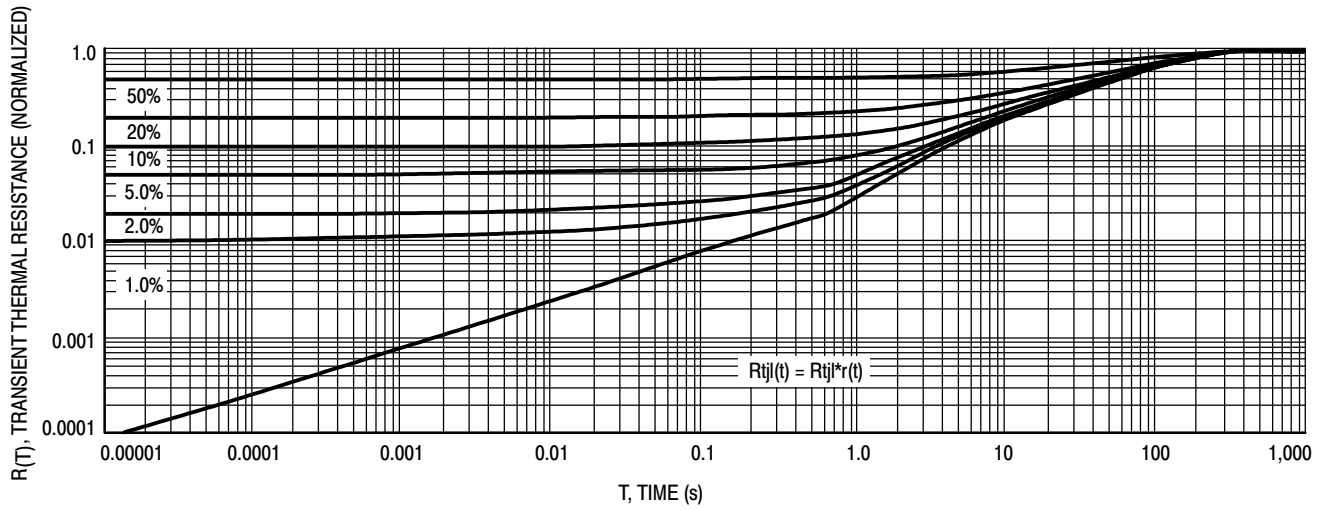
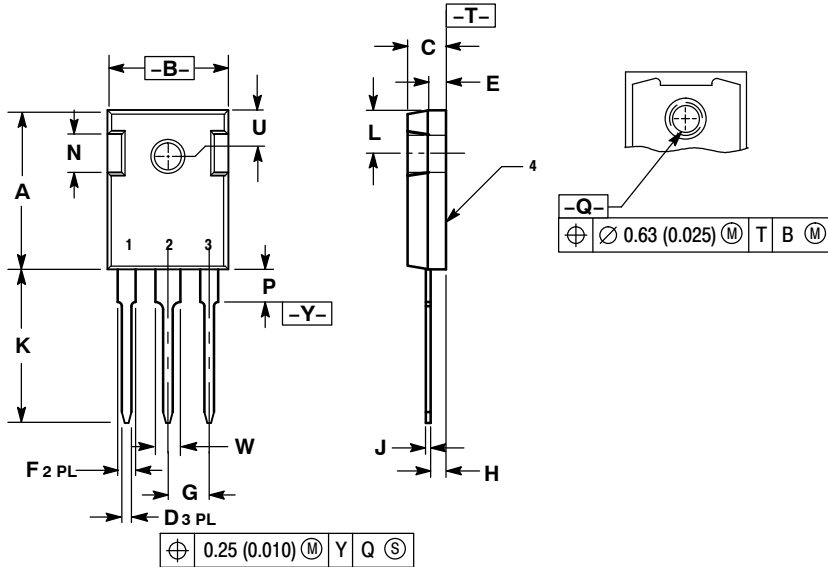


Figure 10. Thermal Response Junction to Ambient (Per Leg)

# MBR4015LWT

## PACKAGE DIMENSIONS

TO-247  
CASE 340L-02  
ISSUE E



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

| DIM | MILLIMETERS |       | INCHES    |       |
|-----|-------------|-------|-----------|-------|
|     | MIN         | MAX   | MIN       | MAX   |
| A   | 20.32       | 21.08 | 0.800     | 0.830 |
| B   | 15.75       | 16.26 | 0.620     | 0.640 |
| C   | 4.70        | 5.30  | 0.185     | 0.209 |
| D   | 1.00        | 1.40  | 0.040     | 0.055 |
| E   | 1.90        | 2.60  | 0.075     | 0.102 |
| F   | 1.65        | 2.13  | 0.065     | 0.084 |
| G   | 5.45 BSC    |       | 0.215 BSC |       |
| H   | 1.50        | 2.49  | 0.059     | 0.098 |
| J   | 0.40        | 0.80  | 0.016     | 0.031 |
| K   | 19.81       | 20.83 | 0.780     | 0.820 |
| L   | 5.40        | 6.20  | 0.212     | 0.244 |
| N   | 4.32        | 5.49  | 0.170     | 0.216 |
| P   | ---         | 4.50  | ---       | 0.177 |
| Q   | 3.55        | 3.65  | 0.140     | 0.144 |
| U   | 6.15 BSC    |       | 0.242 BSC |       |
| W   | 2.87        | 3.12  | 0.113     | 0.123 |

- STYLE 2:
- PIN 1. ANODE
  - 2. CATHODE (S)
  - 3. ANODE 2
  - 4. CATHODES (S)

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**MBR4015LWT/D**



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